ABSTRACT

POLISHING METHOD

A method for polishing an object to form wiring for a semiconductor device includes: removing part of an outside portion of a conductor layer through chemical and mechanical polishing to expose an upper surface of a barrier layer; and removing a remaining part of the outside portion of the conductor layer and an outside portion of the barrier layer through chemical and mechanical polishing to expose an upper surface of an insulator layer. When removing part of the outside portion of the conductor layer, the upper surface of the object is chemically and mechanically polished using a first polishing composition containing a film forming agent. Subsequently, the upper surface of the object is washed to remove a protective film formed on an upper surface of the conductor layer by the film forming agent in the first polishing composition. Thereafter, the upper surface of the object is chemically and mechanically polished again using a second polishing composition containing the film forming agent. Thus, the wiring of the semiconductor device is reliably formed.

Figs. 1A-C

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